



# PD60030 PD60030S

## RF POWER TRANSISTORS The LdmoST Plastic FAMILY

TARGET DATA

Designed for GSM / EDGE / IS-97 applications

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 30\text{ W}$  with 10 dB gain @ 2000 MHz

### DESCRIPTION

The PD60030 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 26 V in common source mode at frequencies of up to 2 GHz. PD60030 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. PD60030's superior linearity performance makes it an ideal solution for base station applications.

The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.

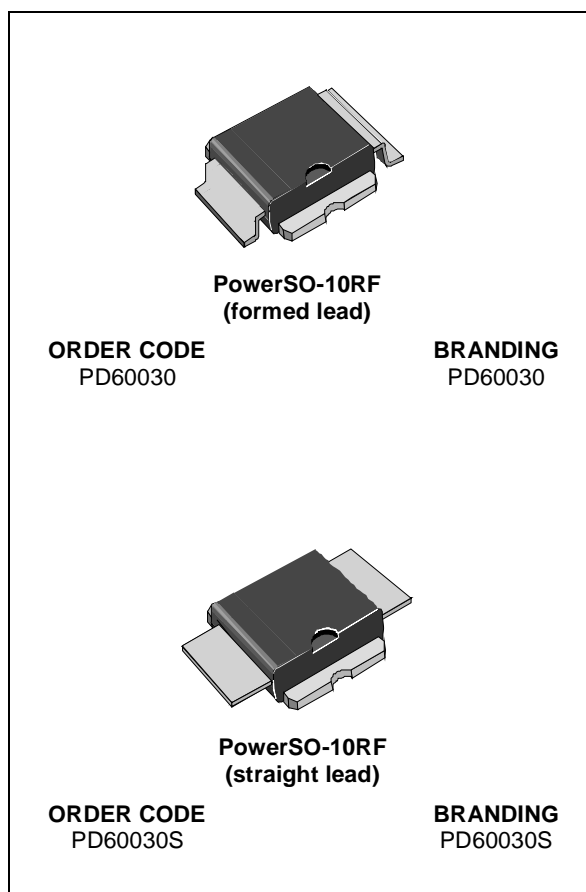
Mounting recommendations are available in [www.st.com/rf/](http://www.st.com/rf/) (look for application note AN1294)

### ABSOLUTE MAXIMUM RATINGS ( $T_{CASE} = 25\text{ }^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	65	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current	TBD	A
$P_{DISS}$	Power Dissipation (@ $T_c = 70\text{ }^{\circ}\text{C}$ )	TBD	W
$T_j$	Max. Operating Junction Temperature	165	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	-65 to +175	$^{\circ}\text{C}$

### THERMAL DATA ( $T_{CASE} = 70\text{ }^{\circ}\text{C}$ )

$R_{th(j-c)}$	Junction -Case Thermal Resistance	TBD	$^{\circ}\text{C/W}$
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PD60030 - PD60030S

ELECTRICAL SPECIFICATION (T<sub>CASE</sub> = 25 °C)

STATIC

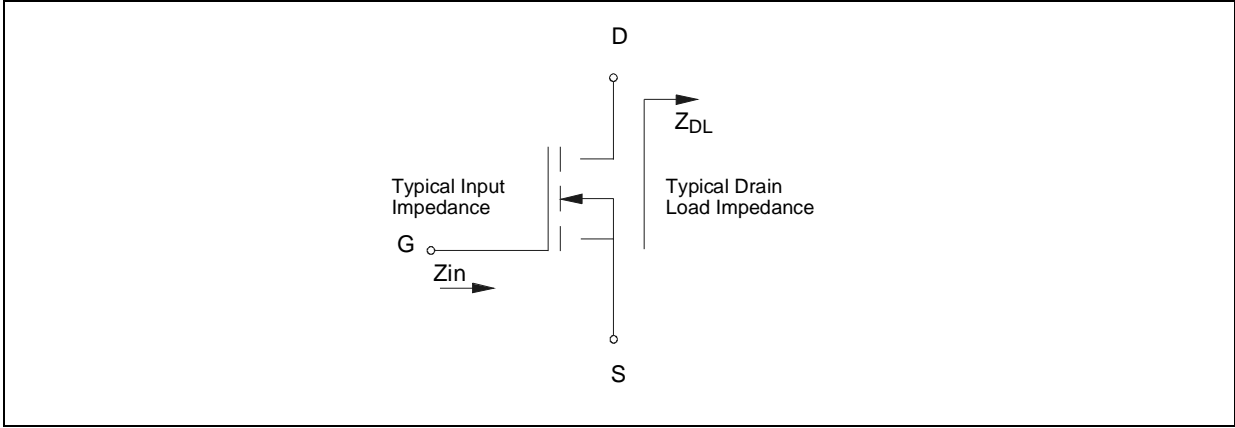
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V	I <sub>DS</sub> = 1 mA	65			V
I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 28 V			1	μA
I <sub>GSS</sub>	V <sub>GS</sub> = 20 V	V <sub>DS</sub> = 0 V			1	μA
V <sub>GS(Q)</sub>	V <sub>DS</sub> = 28 V	I <sub>D</sub> = 300 mA	2.5		5.0	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3 A		TBD		V
G <sub>FS</sub>	V <sub>DS</sub> = 10 V	I <sub>D</sub> = 3 A	2.0	TBD		mho
C <sub>ISS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 28 V		TBD		pF
C <sub>OSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 28 V		TBD		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 28 V		TBD		pF

DYNAMIC

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
P <sub>out</sub>	V <sub>DD</sub> = 26 V	I <sub>DQ</sub> = 300 mA	f = 2000 MHz	30			W
IMD3	V <sub>DD</sub> = 26 V	I <sub>DQ</sub> = 300 mA	P <sub>OUT</sub> = 30 W PEP		-32	-28	dBc
G <sub>PS</sub>	V <sub>DD</sub> = 26 V	I <sub>DQ</sub> = 300 mA	P <sub>OUT</sub> = 30 W PEP	10	11		dB
η <sub>D</sub>	V <sub>DD</sub> = 26 V	I <sub>DQ</sub> = 300 mA	P <sub>OUT</sub> = 30 W PEP		35		%
Load mismatch	V <sub>DD</sub> = 26 V	I <sub>DQ</sub> = 300 mA	P <sub>OUT</sub> = 30 W ALL PHASE ANGLES	10:1			VSWR

note: f<sub>1</sub> = 2000 MHz  
PEP f<sub>2</sub> = 2000.1 MHz

IMPEDANCE DATA

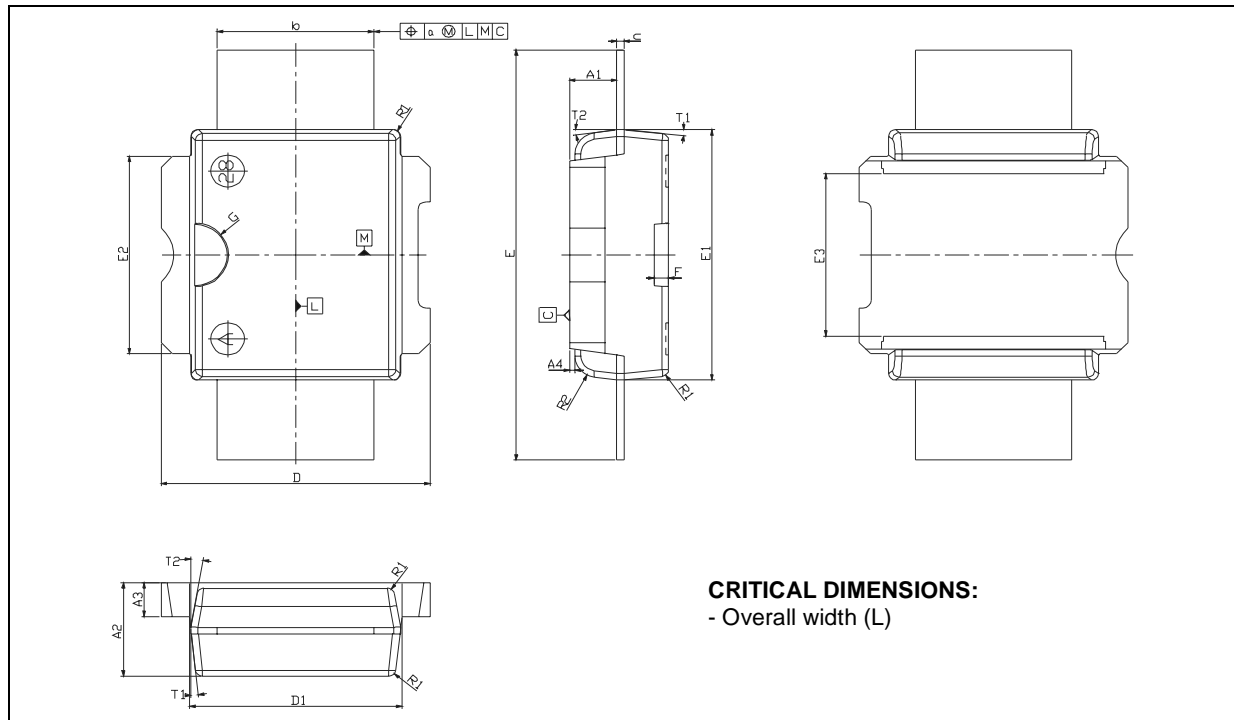


FREQ. MHz	Z <sub>IN</sub> (Ω)	Z <sub>DL</sub> (Ω)
1800		
1850		
1900		
1950		
2000		

**PowerSO-10RF Straight Lead MECHANICAL DATA**

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A1	1.62	1.67	1.72	0.064	0.065	0.068
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	15.15	15.4	15.65	0.595	0.606	0.615
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
R1			0.25			0.01
R2		0.8			0.031	
T1		6 deg			6 deg	
T2		10 deg			10 deg	

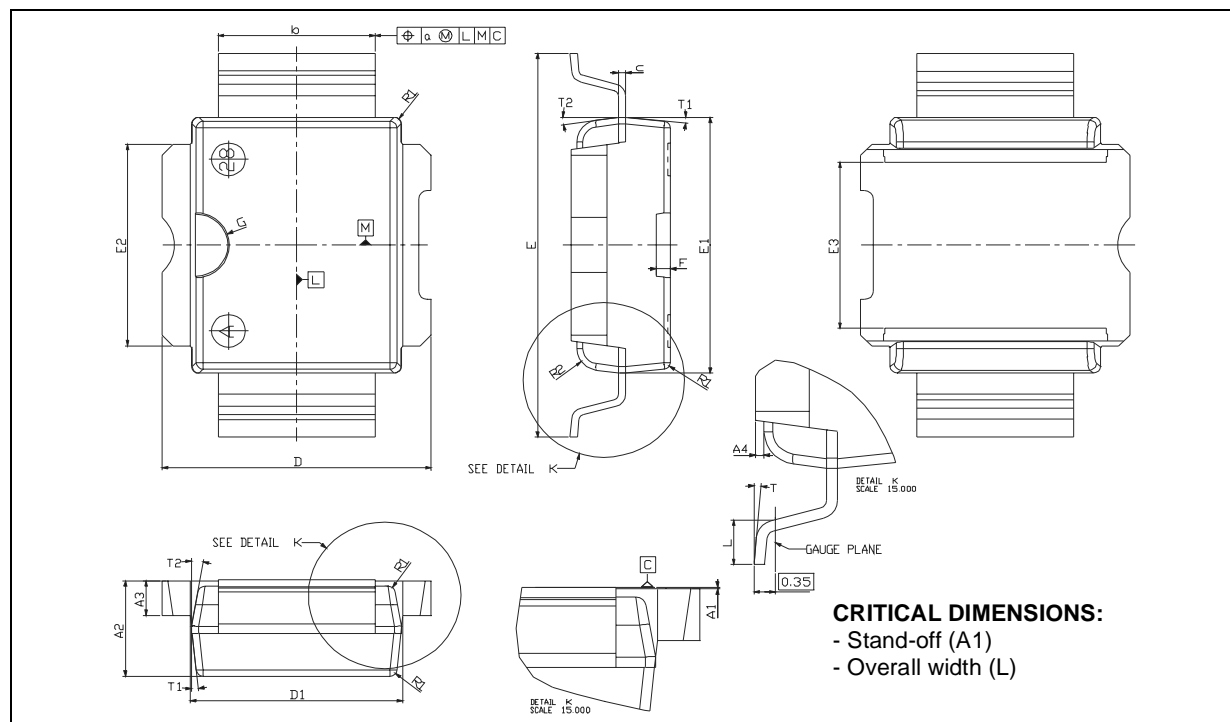
Note (1): Resin protrusions not included (max value: 0.15 mm per side)



**PowerSO-10RF Formed Lead (Gull Wing) MECHANICAL DATA**

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A1	0	0.05	0.1	0.	0.0019	0.0038
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	13.85	14.1	14.35	0.544	0.555	0.565
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
L	0.8	1	1.1	0.030	0.039	0.042
R1			0.25			0.01
R2		0.8			0.031	
T	2 deg	5 deg	8 deg	2 deg	5 deg	8 deg
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note (1): Resin protrusions not included (max value: 0.15 mm per side)



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